Substrate Integrated Waveguide Filters Based on a Dielectric Layer with Periodic Perforations

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Abstract—This paper presents a novel class of substrate integrated waveguide (SIW) filters, based on periodic perforations of the dielectric layer. The perforations allow to reduce the local effective dielectric permittivity, thus creating waveguide sections below cutoff. This effect is exploited to implement immittance inverters through analytical formulas, providing simple design rules for the direct synthesis of the filters. The proposed solution is demonstrated through the design and testing of several filters with different topologies (including half-mode SIW and folded structures). The comparison with classical iris-type SIW filters demonstrates that the proposed filters exhibit better performance in terms of sensitivity to fabrication inaccuracies and rejection bandwidth, at the cost of a slightly larger size.

Index Terms—Filters, resonator filters, substrate integrated waveguide, tolerance analysis.

I. INTRODUCTION

THE SUBSTRATE INTEGRATED WAVEGUIDE (SIW) technology has been the object of intense and evergrowing research activities in the last decade [1], [2]. The SIW technology combines the complete shielding and fairly low losses, with the simple and cost-effective manufacturing, thus representing the ideal platform for the development of the next

generation of wireless systems.

Besides the traditional SIW, several novel structures have been proposed, to reduce the size, increase the single-mode bandwidth, and decrease losses. Among them, the folded SIW [3], [4] allows to reduce by half the width of the waveguide (at the cost of a dual-layer manufacturing), the half-mode SIW [5], [6] reduces the width and increases the single-mode bandwidth of a factor two, the slab SIW [7] allows to increase the single-mode bandwidth, the ridge SIW [8], [9] increases the bandwidth and reduces the size (at the cost of a higher

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Fig. 1. SIW filter with periodic perforations: (*a*) Physical geometry of the filter; (*b*) Equivalent structure based on the homogeneous permittivity of the perforated area.

fabrication complexity), and the empty SIW [10] cuts dielectric losses and extends the power handling capabilities (at the cost of a slightly larger size).

Similarly, a number of novel SIW filter configurations have been presented to improve filter performance, reduce losses, and minimize the footprint [11]-[13]. Half-mode [14], folded [15], and quarter-mode [16] SIW cavities have been adopted to reduce the filter size, and the substrate integrated coaxial line [17] has been used to obtain wide stopband and compact size. The use of defected ground structures and of extracted poles have been proposed in [18], [19] for improving the outof-band rejection. Miniature SIW cavities adopting interdigital capacitors [20] have been proposed to reduce filter dimensions. The use of empty surface-mounted waveguide cavities in [21] allows to implement filters with higher quality factor.

Recently, the preliminary investigation of a band-pass filter based on a periodically drilled SIW structure has been proposed [22]: perforations in the dielectric substrate (Fig. 1(*a*)) allow to reduce the local effective permittivity, thus creating waveguide sections below cutoff (Fig. 1(*b*)). Further developments of this class of filters have been reported in two conference papers [23], [24], adding flexibility to the design and extending this concept to half-mode SIW structures.

In this paper, a systematic investigation of the properties of

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Fig. 2. Equivalent circuit of an in-line *N*-pole filter.

perforated SIW filters is presented. The waveguide sections with reduced permittivity are exploited to implement immittance inverters. A theoretical study of their properties is reported, along with the guidelines for the fine control of the coupling. Simple models and design rules are presented, and applied to the design of four different pass-band SIW filters, namely a classical SIW filter, a half-mode SIW filter, and two half-mode SIW filters in folded topology (which allows the introduction and control of a transmission zero). An interesting feature of the proposed filter is that the physical length of the resonators is extremely short (about $\lambda_g/6$ in the considered examples), thus allowing relatively compact structures despite of the not so compact coupling elements realized by perforated waveguide sections. It is also demonstrated that these filters exhibit lower sensitivity to fabrication inaccuracies compared to iris-type filters with analogous frequency response. This feature of perforated SIW filters opens the possibility of manufacturing microwave filters by low-cost fabrication technique, such as the punching technique [25].

The paper is organized as follows. Section II presents the operation principle of the filter and the modeling of the immittance inverter based on perforated (evanescent mode) SIW sections. Section III presents the synthesis of a four-pole SIW filter, its fabrication and testing, and the assessment of its low sensitivity to fabrication tolerances. Section IV reports the design and testing of a four-pole filter in half-mode SIW topology, to reduce the dimensions. Finally, Section V shows two prototypes of three-pole half-mode SIW filters in folded configuration, which allow the introduction and control of transmission zeros.

II. OPERATION PRINCIPLE OF THE FILTER

The equivalent circuit of the filtering structure in Fig. 1 can be obtained by modeling the evanescent waveguide sections as impedance inverters (plus two transmission lines), and the propagating waveguide sections connecting two evanescent sections as dispersive transmission lines (Fig. 2).

The normalized impedance inverter $K_{i,j}^{(Nor)} = K_{i,j}/Z_0$ can be evaluated directly from the coupling matrix elements

$$K_{S,1}^{(\text{Nor})} = M_{S,1} \sqrt{\frac{\pi}{2} F B W_{\lambda_g}}$$
(1)

$$K_{N,L}^{(\text{Nor)}} = M_{N,L} \sqrt{\frac{\pi}{2}} FBW_{\lambda_g}$$
(2)

$$K_{i,j}^{(\text{Nor})} = M_{i,j} \frac{\pi}{2} FBW_{\lambda_g}$$
(3)



Fig. 3. Evanescent waveguide section: (*a*) Geometry of the evanescent waveguide section; (*b*) Representation as an inverter and two transmission line sections; (*c*) Implementation of a resonator by two inverters.

where the subscripts S and L stand for source and load, while indices i and j refer to the *i*-th and *j*-th resonator, respectively, and N is the total number of resonators. The fractional bandwidth *FBW* is calculated by using the waveguide wavelength to account for dispersion

$$FBW_{\lambda_g} = \frac{\lambda_{g2} - \lambda_{g1}}{\lambda_{g0}} \tag{4}$$

being λ_{g1} and λ_{g2} the waveguide wavelengths at the lower and higher pass-band edge, respectively, while λ_{g0} is the waveguide wavelength at the central frequency:

$$\lambda_{g0} = \sqrt{\lambda_{g1} \lambda_{g2}} \tag{5}$$

A. Synthesis of the immittance inverter

The section with reduced permittivity ε_{r1} (Fig. 3(*a*)) acts as an immittance inverter with two transmission line sections (Fig. 3(*b*)). This equivalence is shown by evaluating the reflection coefficient of the evanescent waveguide section.

The propagation constant β_0 of the input and output waveguides is real, whereas the one of the evanescent waveguide β_1 is purely imaginary

$$\beta_0 = \sqrt{\left(\frac{2\pi}{\lambda}\right)^2} \varepsilon_{r0} - \left(\frac{\pi}{w}\right)^2 \tag{6}$$

$$\beta_1 = -j\gamma_1 = \sqrt{\left(\frac{2\pi}{\lambda}\right)^2} \varepsilon_{r1} - \left(\frac{\pi}{w}\right)^2 \tag{7}$$

where λ is the wavelength in vacuum and *w* is the waveguide width. Analogously, the characteristic impedance Z_0 (in the propagating waveguide section) is real, whereas Z_1 (in the evanescent waveguide section) is imaginary

$$Z_0 = \frac{\omega \mu}{\beta_0} \tag{8}$$

IEEE TRANSACTIONS ON MICROWAVE THEORY AND TECHNIQUES

$$Z_1 = \frac{\omega\mu}{\beta_1} = \frac{\omega\mu}{-j\gamma_1} \tag{9}$$

The input impedance Z_{in} can be expressed as

$$Z_{\rm in} = Z_1 \frac{Z_0 + jZ_1 \tan(\beta_1 l)}{Z_1 + jZ_0 \tan(\beta_1 l)}$$
(10)

where *l* is the length of the evanescent waveguide section. This allows the evaluation of the reflection coefficient Γ

$$\Gamma = S_{11} = \frac{Z_{in} - Z_0}{Z_{in} + Z_0} = \frac{Z_1 \frac{Z_0 + jZ_1 \tan(\beta_1 l)}{Z_1 + jZ_0 \tan(\beta_1 l)} - Z_0}{Z_1 \frac{Z_0 + jZ_1 \tan(\beta_1 l)}{Z_1 + jZ_0 \tan(\beta_1 l)} + Z_0} = \frac{j(Z_1^2 - Z_0^2) \tan(\beta_1 l)}{Z_0 Z_1 + j(Z_1^2 + Z_0^2) \tan(\beta_1 l)} = \frac{j(Z_1^2 - Z_0^2) \tan(\beta_1 l)}{2j\gamma_1\beta_0 + (\gamma_1^2 - \beta_0^2) \tanh(\gamma_1 l)} = \frac{(\gamma_1^2 + \beta_0^2) \tanh(\gamma_1 l)}{\sqrt{4(\gamma_1\beta_0)^2 + (\gamma_1^2 - \beta_0^2)^2 \tanh(\gamma_1 l)}} \times \frac{e^{-j \arctan\left(\frac{2\gamma_1\beta_0}{(\gamma_1^2 - \beta_0^2) \tanh(\gamma_1 l)}\right)}}{e^{-j \arctan\left(\frac{2\gamma_1\beta_0}{(\gamma_1^2 - \beta_0^2) \tanh(\gamma_1 l)}\right)}}$$
(11)

Therefore, with reference to the Appendix, the evanescent waveguide section can be represented by an impedance inverter and two transmission line sections, as shown in Fig. 3(b). In fact, the normalized inverter of value

$$K^{(\text{Nor})} = \frac{K}{Z_0} = \sqrt{\frac{1 + S_{11}^{(\text{Ampl})}}{1 - S_{11}^{(\text{Ampl})}}}$$
(12)

with

$$S_{11}^{(\text{Ampl})} = -\frac{(\gamma_1^2 + \beta_0^2) \tanh(\gamma_1 l)}{\sqrt{4(\gamma_1 \beta_0)^2 + (\gamma_1^2 - \beta_0^2)^2 \tanh^2(\gamma_1 l)}}$$
(13)

accounts for the return loss amplitude of the evanescent waveguide section, while the transmission line sections at the inverter ports with length

$$\Lambda = \frac{1}{2\beta_0} \arctan\left(\frac{2\gamma_1\beta_0}{\left(\gamma_1^2 - \beta_0^2\right)\tanh(\gamma_1 l)}\right)$$
(14)

take into account the return loss phase.

In conclusion, (12) and (14) provide analytical formulas for the design of the impedance inverter in Fig. 3(b).



Fig. 4. Model of the evanescent waveguide section: (*a*), (*b*), (*c*) Three different configurations of the perforated evanescent waveguide section; (*d*) Normalized impedance inverter values $K^{(Nor)}$ versus the central gap *a* (*w* = 16.8 mm, $\varepsilon_r = 10$, radius of the holes r = 0.85 mm, and distance between adjacent holes $\Delta = 0.25$ mm); (*e*) Line length Λ versus the central gap *a*.

B. Implementation of the Evanescent Mode Section

The evanescent waveguide section can be obtained by exploiting perforations in the substrate to reduce the dielectric constant, as shown in Fig. 4(*a*). The perforated substrate exhibits an effective dielectric permittivity ε_{eff} , which assumes an intermediate value between the permittivity of the substrate and of the air [22]. The effective permittivity ε_{eff} is computed as the dielectric permittivity of the homogeneous SIW structure with the same cutoff frequency of the fundamental mode.

With reference to Fig. 4(*a*), the desired impedance inverter value can be obtained by applying (11) and considering $\varepsilon_{r1} = \varepsilon_{eff}$. As an example, considering a waveguide width of

TABLE I Impedance Inverter Associated to Perforated Evanescent Waveguide Lengths (in millimeters)						
	Normalized K-inverter		Transmission line length Λ			
Number of hole columns	Full-wave (HFSS)	Equation $(\epsilon_{eff}=5)$	Full-wave (HFSS)	Equation $(\epsilon_{eff}=5)$		
1	0.8231	0.8467	5.332	5.552		
2	0.6791	0.7000	5.648	5.864		
3	0.5622	0.5814	5.923	6.139		
4	0.4673	0.4843	6.150	6.368		
5	0.3901	0.4049	6.330	6.551		
6	0.3268	0.3398	6.468	6.693		

w=16.8 mm, a dielectric constant $\varepsilon_r=10$, and holes with radius of r=0.85 mm and a side-by-side distance of $\Delta=0.25$ mm, the effective dielectric constant is $\varepsilon_{eff}=5$. Considering this effective dielectric constant and using (12) and (14), an estimation of the equivalent K-inverter and of the transmission line lengths Λ can be found (Fig. 3(*b*)). The lengths of the evanescent perforated waveguide sections considered in (12) and (14) are related to the number of hole columns (1.7 mm, 3.65 mm, 5.6 mm, 7.55 mm, 9.5 mm, 11.45 mm). In Table I, such results are compared to simulations from the full-wave solver Ansys High Frequency Structural Simulator (HFSS), showing a good agreement.

The limitation of such a structure is that the length of the evanescent waveguide section depends on the number of hole columns, and only discrete values are possible. Instead, the filter design requires a more accurate selection of K-inverter values. To overcome this problem, the structure in Fig. 4(*b*), obtained by removing the top and bottom hole rows, is adopted. Note that this removal slightly changes the K-inverter value, as removed holes are those positioned where the field is weaker. However, it creates enough space to shift the holes, increasing the gap *a* between the central hole rows (Fig. 4(*c*)).

The idea is to use the number of hole columns for a coarse selection of the K-inverter (by using the analytical formulas) and then refine the value by selecting the proper gap a (by using full-wave simulations). This concept is illustrated in Fig. 4(d), where the K-inverter values related to perforated evanescent waveguide sections having a number of hole columns ranging from 1 to 6 are plotted as a function of the gap a. Note that, exploiting the further degree of freedom of the gap a, all possible K-inverter values in the range from 0.34 to 0.91 are attainable. Values lower than 0.34 can be easily obtained by using more than 6 hole columns, while to obtain values larger than 0.91 it is necessary to vary the geometry by reducing the hole radius or increasing the distance between adjacent holes. Finally, in Fig. 4(e) the diagram for the evaluation of the transmission line lengths Λ to be added to the K-inverter ports is shown. The results of Fig. 4(d) and Fig. 4(e) have been obtained from the full-wave solver Ansys HFSS.

A wide range of coupling coefficients can be achieved by changing the number of hole columns and the central gap *a*. This allows to design filters with large or narrow passband.



Fig. 5. Synthesis of the four-pole filter with perforations: (a) Coupling matrix of the filter obtained from the synthesis; (b) Geometry of the filter (dimensions in mm: $d_1=7.15$, $d_2=7.44$, $a_1=4.32$, $a_2=1$, $a_3=0.63$, and w=16.8); (c) Scattering parameters (results from the synthesis are compared with the HFSS simulation).

In particular, narrow band filters require small coupling, which can be obtained by increasing the length of the waveguide sections below cutoff (i.e., the number of hole columns).

III. FILTER BASED ON PERFORATED SIW

A. Preliminary Synthesis of the Filter

As an example, the design of an in-line filter centered at $f_0=3.65$ GHz with a fractional bandwidth of *FBW*=0.16, described by the coupling matrix shown in Fig. 5(*a*) is here considered.

The first step is the evaluation of the normalized Kinverters by using (1)-(3), thus obtaining $K_{S,1}^{(Nor)} = K_{4,L}^{(Nor)} = 0.75, K_{1,2}^{(Nor)} = K_{3,4}^{(Nor)} = 0.515, K_{2,3}^{(Nor)} = 0.425.$

The design procedure consists in the use of (12)-(14) to find the lengths l of the evanescent waveguide sections by using the effective dielectric constant of the perforated waveguide (in this case ε_{eff} =5). The resulting lengths are l_1 =2.9 mm, l_2 =6.9 mm and l_3 =9.0 mm. Such lengths can be approximated by a number of hole columns equal to 2, 4 and 5, respectively. This corresponds, for the structure of Fig. 4(*b*), to normalized K-inverters of value 0.69, 0.48, and 0.41, respectively. Fine tuned K-inverter values are then obtained by a proper selection of the gap a, with the help of a full-wave simulator. Note that the starting value of the K-inverters should be lower than the desired one, as gap a only allows the increase of this value. This means that the distances l_1 , l_2 , and l_3 should be rounded to the higher integer.

A faster design procedure is possible by exploiting the diagram of Fig. 4(d), to directly find the number of hole columns and the gap a. Note that the same value of K-inverter can be obtained by using different hole column numbers. As an example, the K-inverter value 0.75 can be obtained by using 2 or 3 columns, the value 0.515 with 4, 5 or 6 columns, while the value 0.425 with 5 or 6 columns. In this example, K_{S1} has been realized by using 3 columns and $a_1 = a_5 = 4.32$ mm, K_{12} by using 4 columns and $a_2=a_4=1$ mm, K_{23} by using 4 columns and $a_3=0.63$ mm. By using the diagram of Fig. 4(e) it is possible to find the length of the transmission lines to be added to the K-inverter: $\Lambda_1 = 6.87$ mm, $\Lambda_2 = 6.45$ mm, and $\Lambda_3=6.58$ mm. Such lengths are then subtracted from the resonator ($\lambda_g/2=20.47$ mm), leading to a physical resonator of length $d_1 = d_4 = 20.47 - 6.87 - 6.45 = 7.15$ mm and $d_2 = d_3 = 20.47 - 6.45 = 7.15$ 6.45-6.58=7.44 mm (Fig. 5(b)).

In Fig. 5(c), the scattering parameters of the designed filter are compared to the coupling matrix response, showing a very good agreement even though the filter was not optimized.

An interesting feature of this structure is the reduced physical length of the resonators. In fact, while the length of the transmission lines in Fig. 2 is $\lambda_g/2$, the length of the resonator in the physical structure is significantly reduced, resulting in about $\lambda_g/6$ in this example. This reduction, according to Fig. 3(*c*), is due to the presence of the transmission line sections in the impedance inverter representing the evanescent waveguide sections. This phenomenon also happens in other filtering structures, such as in iris filters, but the resonator length reduction is very limited in those cases. As discussed in Section II, narrower band filters require longer evanescent waveguide sections, thus increasing the size of the filter.

B. Manufacturing and Experimental Validation

Based on the results of the filter synthesis discussed in the previous subsection, the final geometry of the prototype has been obtained. First of all, the equivalent rectangular waveguide adopted in the synthesis has been replaced by the SIW structure [26], using metal vias with a diameter of d=1 mm and longitudinal spacing of s=1.5 mm to avoid radiation leakage [2]. Moreover, tapered transitions have been added to connect the SIW structure to the input and output microstrip lines, required for measurement purposes. A light full-wave optimization (based on the commercial electromagnetic solver HFSS) was adopted to achieve the final coupling matrix (Fig. 6(a)) and geometrical dimensions of the filter (Fig. 6(b)).

The filter has been fabricated by using a dielectric substrate Taconic CER-10, with a thickness of 0.64 mm, relative dielectric permittivity of ε_r =10.0, loss tangent tan δ =0.0035,

and metal conductivity σ =5.8·10⁷ S/m. An LPKF E33 milling machine was adopted to pattern the metal layers and to drill the holes through the substrate, and conductive paste was used to metalize the via holes of the side walls. A picture of the prototype is shown in Fig. 6(*c*). The air holes have been closed by copper tape on both sides (not shown in the picture), to avoid any radiation leakage. A more standard manufacturing process could be the one adopted in [10], based on multilayered printed-circuit board technology.



Fig. 6. Prototype of the four-pole filter based on perforated SIW structure: (a) Coupling matrix of the optimized filter; (b) Geometry of the filter (dimensions in mm: v=0.6, b=2.6, $d_1=10$, $d_2=7.95$, $a_1=4$, $a_2=0.55$, $a_3=0.25$, w=17.8, c=7, and l=81); (c) Photograph of the prototype; (d) Scattering parameters of the four-pole filter (HFSS simulation compared with measured data).



Fig. 7. Performance comparison between the perforated SIW filter and a classical iris-type SIW filter: (a) Geometry of the iris-type SIW filter (dimensions in mm: v=0.6, b=3.03, $d_1=15.25$, $d_2=15.1$, $a_1=13.3$, $a_2=12.1$, $a_3=11.4$, w=17.425, c=9.5, and l=62.7); (b) Scattering parameters of the perforated SIW filter and the iris-type SIW filter (HFSS simulation).

The prototype has been experimentally characterized: measurements were performed in the frequency band from 2.5 GHz to 5.5 GHz by using an Anritsu Universal Test Fixtures (UTF) 3680 and an Anritsu 37347C vector network analyzer (VNA). No de-embedding was applied to the measured results, to remove the connectors and transitions effect. The comparison between HFSS simulations and the measurements is shown in Fig. 6(d). The small discrepancy is attributed to the combined effect of dielectric permittivity variation and of fabrication inaccuracies (*e.g.*, in the top/bottom metal plates). As a consequence, there is a small shift in the measured position of the filter poles: this determines a slightly narrower pass bandwidth of the filter and a higher out-of-band rejection in the measurement than in the simulation.

The bandwidth, defined at 10 dB input matching, is 630 MHz in the measurement and 660 MHz in the simulation. The measured insertion loss is 1.31 dB at the central frequency $f_0=3.65$ GHz, compared to 1.15 dB in the simulation.

The simulation allows to investigate the different contribution of losses. Each transition contributes with a loss of 0.19 dB, whereas the SIW filter loss is 0.77 dB, attributed to the dielectric loss (0.47 dB), and to the conductor loss (0.30 dB). There is practically no radiation loss in the filter (0 dB). The size of the circuit is $l \times w = 1442$ mm².

C. Comparison with Equivalent Inductive Iris Filter

To assess the advantages of the proposed structure, the perforated filter of Fig. 6 is compared with an inductive iris



Fig. 8. Sensitivity analysis of the iris-type SIW filter and the perforated SIW filter: (*a*) Spread of the scattering parameters of the iris-type SIW filter; (*b*) Spread of the scattering parameters of the perforated SIW filter (HFSS simulation).

filter, with similar filtering characteristics (same central frequency f_0 , number of poles, pass bandwidth, and input matching level), realized on the same dielectric substrate.

The iris-type filter was optimized by using HFSS, and the final geometry is shown in Fig. 7(*a*). The simulation results of the iris-type filter and of the perforated filter of Fig. 6 are compared in Fig. 7(*b*). While the insertion loss in the passband is almost identical for the two filters (1.19 dB in the iris-type SIW filter and 1.15 dB in the perforated filter), the perforated filter exhibits a better performance in the out-of-band rejection (with the spurious band appearing at $1.45f_0=5.22$ GHz in the perforated filter and at $1.32f_0=4.77$ GHz in the iris filter). In terms of dimension, the footprint area of the iris filter is 24% smaller than the perforated filter (1091 mm² compared with 1442 mm²).

The perforated filter exhibits outstanding performance over the iris filter in terms of tolerance to fabrication inaccuracies. To investigate the filter tolerance, a Montecarlo analysis was performed by running 2000 HFSS simulations. The position of all the iris posts was changed independently, with a maximum displacement of 50 µm. Analogously, in the perforated filter,



Fig. 9. Sensitivity analysis of the iris-type SIW filter and the perforated SIW filter with respect to the substrate dielectric permittivity (ϵ_i =9.8±0.2): (*a*) Spread of the scattering parameters of the iris-type SIW filter; (*b*) Spread of the scattering parameters of the perforated SIW filter (HFSS simulation).

the position of the perforated areas was changed with a maximum displacement of 50 μ m; the relative position of the holes in each area was not modified, as the global shift represents the major effect in case of manufacturing by punching [25]. The two filters were compared in Fig. 8, which shows that the spread of the scattering parameters in the passband is more limited in the case of the perforated filter.

The deviation in the substrate dielectric permittivity is another potential source of error, able to jeopardize the filter performance. To investigate this effect and compare the perforated SIW filter and a classical iris-type SIW filter, the frequency response of the two structures was simulated in the case of nominal dielectric permittivity (ε_r =9.8) and in the cases of a deviation of ±0.2. Fig. 9 shows that in both structures the deviation in the dielectric permittivity determines a frequency shift, with no degradation of the bandwidth and the input matching level. More specifically, the frequency shift resulted ±35 MHz both in the case of the perforated SIW filter (Fig. 9(*a*)) and in the case of the iris-type SIW filter (Fig. 9(*b*)).

IV. FILTER BASED ON PERFORATED HALF-MODE SIW

The same filter concept was applied to the half-mode SIW structure, with the aim to reduce the size of the filter. The half-mode SIW filter is obtained by removing half of the top metal layer, with a subsequent HFSS re-optimization. The geometry of the filter and the final dimensions are shown in Fig. 10(a).

A prototype has been fabricated by milling machining, using the same manufacturing process described in the previous section, and a picture of the top layer is shown in Fig. 10(b).

The comparison of simulated and measured scattering parameters is reported in Fig. 10(*c*), in the frequency band from 2.5 GHz to 5.5 GHz. The filter bandwidth, defined at 10 dB input matching, is 730 MHz in the simulation and 760 MHz in the measurement. The insertion loss at the central frequency f_0 =3.65 GHz is 2.40 dB in the simulation and 2.15 dB in the measurement. Also in this case, the different contribution of losses have been investigated through simulations. Each transition contributes with a loss of 0.48 dB, whereas the SIW filter loss is 1.44 dB, which is attributed to dielectric loss (0.63 dB), conductor loss (0.43 dB), and to radiation loss (0.63 dB). The size of the circuit is significantly reduced to the case of the filter in Fig. 6, being the footprint area $l \times w$ =690 mm².

The frequency response of the filter, reported in Fig. 10(c), shows that the insertion loss is larger in the lower portion of the pass band, both in measured and simulated results. To provide a physical insight of this phenomenon, a modal analysis has been performed. In fact, the filter structure can be considered as a cavity resonator, supporting four resonant modes in the pass band of the filter.

The mode spectrum was calculated by using the eigenvalue solver of HFSS. The eigenvalue analysis has been performed under two different boundary conditions of the air box surrounding the cavity: with perfect electric wall boundary condition (where losses depend on dielectric loss and finite metal conductivity, but there is no radiation), and with radiation condition (where also radiation leakage is considered). The electric field amplitude of the four modes is practically unchanged in the two cases, and it is plotted in Fig. 11.

In Table II, the resonance frequencies and the quality factors of the modes are reported, for two cases: in the first case, only conductor and dielectric losses are considered (no radiation), whereas in the second case all sources of loss (conductor, dielectric, and radiation) are taken into account. The resonance frequencies of the four modes exhibit a very limited variation between the two cases, and practically coincide with the four poles of the frequency response of the filter (Fig. 10(c)).

Conversely, the quality factors are significantly affected by radiation: in particular, the first mode reduces its quality factor from 187 to 61. The physical explanation of this effect can be found in the field distribution along the open boundary of the half-mode SIW: in the first mode, the electric field exhibits a uniform phase, thus leading to a non-negligible radiation



Fig. 10. Prototype of the four-pole filter based on perforated half-mode SIW structure: (a) Geometry of the filter (dimensions in mm: v=0.6, b=1.6, $d_1=9.6$, $d_2=8.35$, $a_1=1$, $a_2=0.2$, $a_3=0.4$, w=8.3, c=7, and l=83); (b) Photograph of the prototype; (c) Scattering parameters of the four-pole filter (HFSS simulation compared with measured data).

leakage. This reduction in the quality factor is more significant for the first and second mode, and it is marginal for the other two modes. For instance, in the fourth mode, the alternate phase of the electric field along the open boundary leads to very limited radiation. The variation of the modal quality factors determines the slope of the insertion loss of the filter.

TABLE II Resonance Frequency and Quality Factor of the First Modes of the Perforated Half-Mode SIW Cavity

	Conductor and		Conductor, dielectric	
	Frequency (GHz)	Quality Factor	Frequency (GHz)	Quality Factor
Mode 1	3.30	187	3.19	61
Mode 2	3.44	186	3.28	103
Mode 3	3.70	185	3.55	146
Mode 4	4.00	198	3.90	184



Fig. 11. Amplitude of the electric modal field of the first resonant modes of the perforated half-mode SIW cavity: (*a*) First mode; (*b*) Second mode; (*c*) Third mode; (*d*) Fourth mode.

V. FOLDED FILTER BASED ON PERFORATED HALF-MODE SIW

A folded filter configuration was adopted to mitigate radiation losses of the half-mode SIW filter (Fig. 12(a)). By using this configuration, the open boundaries of the SIW structure are located face-to-face: this allows to reduce the radiation loss, especially for the first cavity mode, where the field exhibits a uniform phase along the entire open boundary. Moreover, the folded configuration introduces a direct inputoutput coupling, which determines transmission zero in the frequency response.

A three-pole half-mode SIW filter in folded configuration was designed by using HFSS. The design is aimed to locate the transmission zero close to the pass band. The geometry of the filter and the final dimensions are shown in Fig. 12(a). A prototype has been fabricated by milling machining, and a picture of the filter is shown in Fig. 12(b).

The comparison of simulated and measured scattering parameters is reported in Fig. 12(*c*), in the frequency band from 2.0 GHz to 7.0 GHz. The filter bandwidth, defined at 10 dB input matching, is 735 MHz in the simulation and 800 MHz in the measurement. The frequency of the transmission zero is 4.65 GHz in the simulation and 4.59 GHz in the measurement. The insertion loss at the central frequency f_0 =3.65 GHz is 1.25 dB in the simulation and 1.20 dB in the measurement. Also in this case, the different contribution of losses have been investigated through simulations. Each transition contributes with a loss of 0.40 dB, whereas the SIW filter loss is 0.45 dB, which is attributed to dielectric loss (0.28 dB), and conductor loss (0.17 dB), and the contribution of radiation loss is negligible (0 dB). The primary effect of the

absence of radiation leakage is the flat insertion loss, as shown in Fig. 12*c*. The size of the circuit is practically identical to the half-mode SIW filter in Fig. 10, being the footprint area $(l+d_3+d_4)\times(2w+g)=693$ mm².

A different three-pole half-mode SIW filter in folded configuration was designed, to demonstrate that the frequency of the transmission zero can be easily controlled by changing the gap g (Fig. 12(a)). In this second design, the transmission zero was located at a higher frequency, with the aim to broaden the out-of-band rejection of the filter. The geometry of the filter is shown in Fig. 12(a), and the final dimensions are given in the caption of Fig. 13. A prototype has been fabricated by milling machining, and a picture of the filter is shown in Fig. 13(a).



The comparison of simulated and measured scattering parameters is reported in Fig. 13(b), in the frequency band from 2.0 GHz to 7.0 GHz. The filter bandwidth, defined at 10 dB input matching, is 718 MHz in the simulation and 795 MHz in the measurement. A broad out-of-band rejection is found in the frequency response, with the transmission below -20 dB from 4.54 GHz to 6.02 GHz in the simulation, and from 4.54 GHz to 6.13 GHz in the measurement. The insertion loss at the central frequency f_0 =3.65 GHz is 1.33 dB in the simulation and 1.68 dB in the measurement. Also in this case, the different contribution of losses have been investigated through simulations. Each transition contributes with a loss of 0.40 dB, whereas the SIW filter loss is 0.53 dB, which is attributed to dielectric loss (0.30 dB), conductor loss (0.19 dB), and very small radiation loss (0.04 dB). The size of the circuit is slightly larger than the one of the filter in Fig. 12, being the footprint area $(l+d_3+d_4)\times(2w+g)=728 \text{ mm}^2$. It is worth noting that, while this filter does not exhibit outstanding out-of-band performance, the proposed filter geometry allows to improve the out-of-band rejection while keeping small size and easy fabrication.



Fig. 12. Prototype of the first three-pole folded filter based on perforated halfmode SIW structure: (*a*) Geometry of the filter (dimensions in mm: v=0.6, b=2.6, $d_1=1.65$, $d_2=10.56$, $d_3=3.9$, $d_4=6.7$, $a_1=2.45$, $a_2=1.95$, $a_3=5$, $a_4=9.45$, w=9.2, c=7, g=1, l=25.1); (*b*) Photograph of the prototype; (*c*) Scattering parameters of the three-pole filter (HFSS simulation compared with measured data).

Fig. 13. Prototype of the second three-pole folded filter based on perforated half-mode SIW structure (dimensions in mm: v=0.6, b=2.6, $d_1=1.65$, $d_2=10.56$, $d_3=3.9$, $d_4=6.7$, $a_1=2.45$, $a_2=1.95$, $a_3=5$, $a_4=9.45$, w=9.2, c=7, g=2, l=25.1): (a) Photograph of the prototype; (b) Scattering parameters of the three-pole filter (HFSS simulation compared with measured data).

VI. CONCLUSION

A new class of substrate integrated waveguide filters has been proposed in this paper. The use of periodic perforations in the dielectric substrate allows to introduce evanescent waveguide sections, which behave as immitance inverters. This solution leads to the design of compact resonators and filters with low sensitivity to fabrication inaccuracies.

Analytical formulas for the design of the immitance inverters have been derived, which represent a useful tool for the direct synthesis of filters. The use of full-wave simulations for the fine tuning of the inverter geometry has been also discussed.

Four SIW filters have been designed and experimentally validated. They allow to demonstrate the feasibility of the proposed structures and the usefulness of the design formulas, the filter performance in comparison with iris-type filters, the effect of radiation loss in the case of half-mode SIW structures and the technique to mitigate this loss, and the possibility to introduce and control transmission zeros.

APPENDIX

The ABCD matrix of an impedance inverter is

$$\begin{bmatrix} A & B \\ C & D \end{bmatrix} = \begin{bmatrix} 0 & jK \\ j/K & 0 \end{bmatrix}$$
(15)

and the corresponding scattering matrix is

$$[S] = \frac{1}{K^2 + Z_1 Z_2} \begin{bmatrix} K^2 - Z_1 Z_2 & j 2K \sqrt{Z_1 Z_2} \\ j 2K \sqrt{Z_1 Z_2} & K^2 - Z_1 Z_2 \end{bmatrix}$$
(16)

being Z_1 and Z_2 the reference impedance of port 1 and 2, respectively. In the particular case of $Z_1 = Z_2 = Z_0$

$$[S] = \frac{1}{K^2 + Z_0^2} \begin{bmatrix} K^2 - Z_0^2 & j2KZ_0 \\ j2KZ_0 & K^2 - Z_0^2 \end{bmatrix}$$
(17)

when Z_0 is real, $S_{11} = S_{22}$ is real while $S_{21} = S_{12}$ is imaginary. Considering that this is a scattering matrix of a lossless component, S_{22} is completely determined by S_{11} (apart for the sign). This means that each component having S_{11} real is an impedance inverter and its value can be evaluated as

$$K = \sqrt{Z_1 Z_2} \sqrt{\frac{1 + S_{11}}{1 - S_{11}}}$$
(18)

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IEEE TRANSACTIONS ON MICROWAVE THEORY AND TECHNIQUES

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